

XN5601

Silicon PNP epitaxial planer transistor (Tr1)
Silicon NPN epitaxial planer transistor (Tr2)

For general amplification

Features

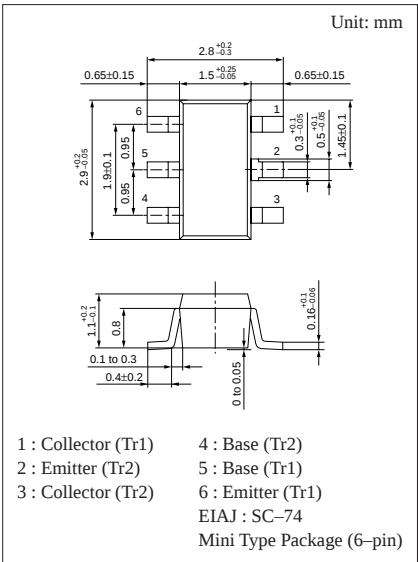
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

- 2SB709A+2SD601A

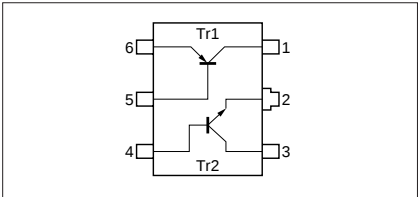
Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Ratings	Unit
Tr1	Collector to base voltage	V_{CBO}	-60	V
	Collector to emitter voltage	V_{CEO}	-50	V
	Emitter to base voltage	V_{EBO}	-7	V
	Collector current	I_C	-100	mA
	Peak collector current	I_{CP}	-200	mA
Tr2	Collector to base voltage	V_{CBO}	60	V
	Collector to emitter voltage	V_{CEO}	50	V
	Emitter to base voltage	V_{EBO}	7	V
	Collector current	I_C	100	mA
	Peak collector current	I_{CP}	200	mA
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	°C
	Storage temperature	T_{stg}	-55 to +150	°C



Marking Symbol: 4N

Internal Connection



■ Electrical Characteristics (Ta=25°C)

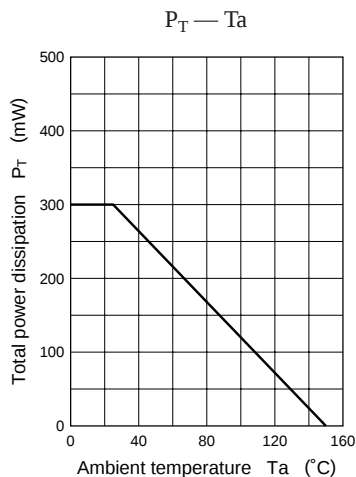
● Tr1

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-60			V
Collector to emitter voltage	V_{CEO}	$I_C = -2mA, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-7			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
	I_{CEO}	$V_{CE} = -10V, I_B = 0$			-100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10V, I_C = -2mA$	160		460	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.3	-0.5	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 1mA, f = 200MHz$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.7		pF

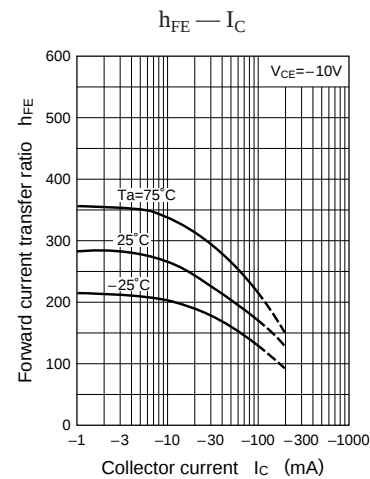
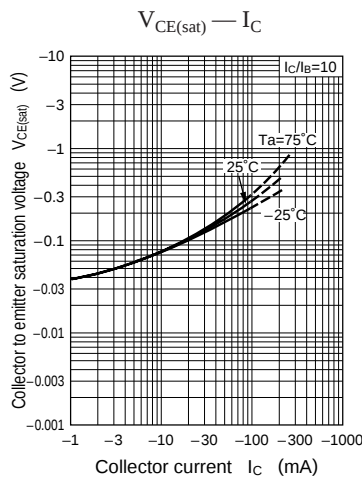
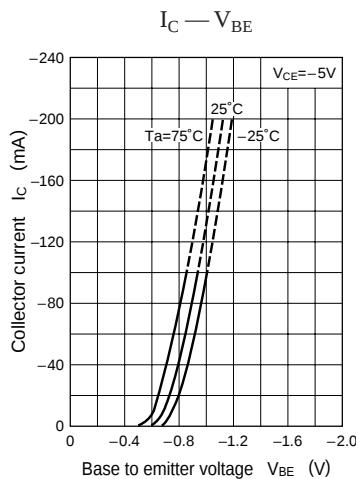
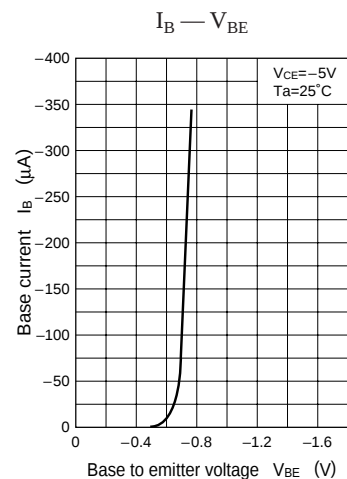
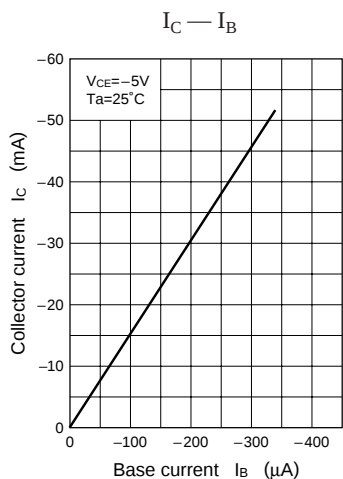
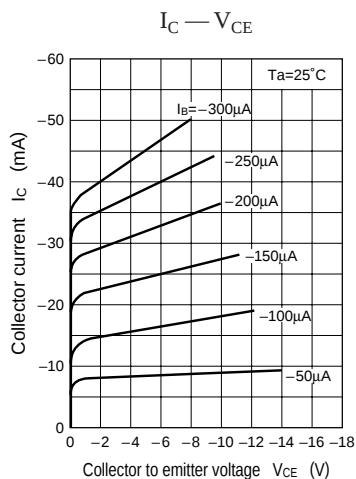
● Tr2

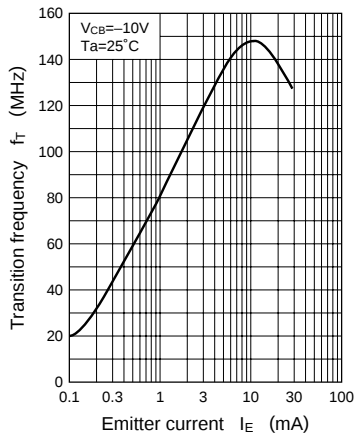
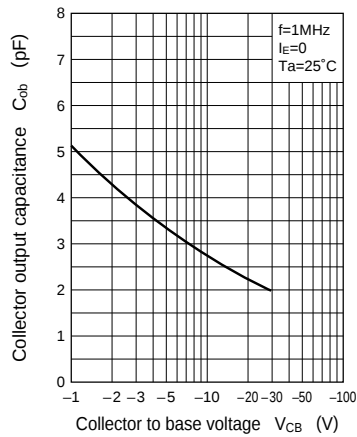
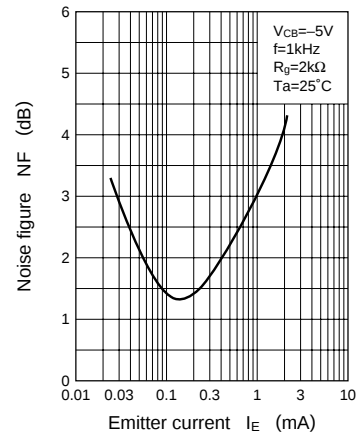
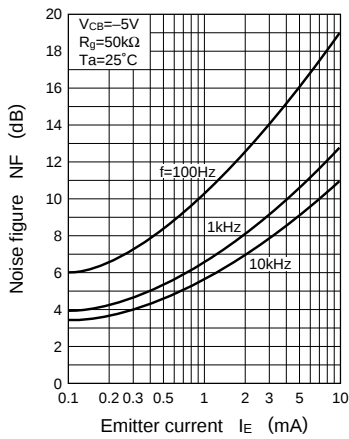
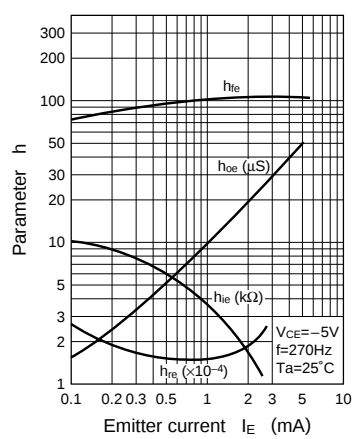
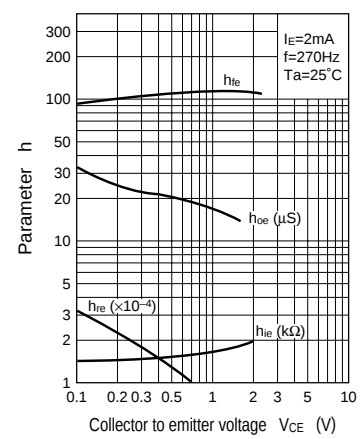
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	60			V
Collector to emitter voltage	V_{CEO}	$I_C = 2mA, I_B = 0$	50			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	7			V
Collector cutoff current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 10V, I_B = 0$			100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10V, I_C = 2mA$	160		460	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 10mA$		0.1	0.3	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		3.5		pF

Common characteristics chart

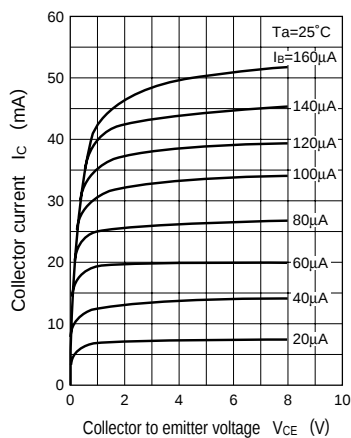
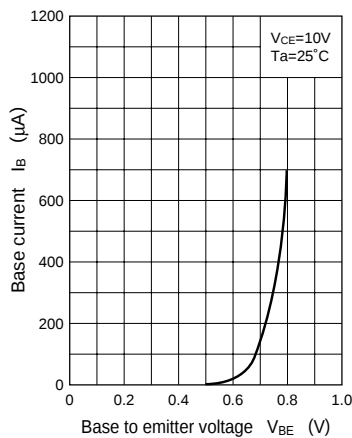


Characteristics charts of Tr1



$f_T - I_E$  $C_{ob} - V_{CB}$  $NF - I_E$  $NF - I_E$  h Parameter — I_E  h Parameter — V_{CE} 

Characteristics charts of Tr2

 $I_C - V_{CE}$  $I_B - V_{BE}$  $I_C - V_{BE}$ 